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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I ² C, IrDA, LINbus, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f411ceu7

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2 Description

The STM32F411xC/xE devices are based on the high-performance ARM® Cortex®-M4 32-bit RISC core operating at a frequency of up to 100 MHz. The Cortex®-M4 core features a Floating point unit (FPU) single precision which supports all ARM single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F411xC/xE belongs to the STM32 Dynamic Efficiency™ product line (with products combining power efficiency, performance and integration) while adding a new innovative feature called Batch Acquisition Mode (BAM) allowing to save even more power consumption during data batching.

The STM32F411xC/xE incorporate high-speed embedded memories (up to 512 Kbytes of Flash memory, 128 Kbytes of SRAM), and an extensive range of enhanced I/Os and peripherals connected to two APB buses, two AHB bus and a 32-bit multi-AHB bus matrix.

All devices offer one 12-bit ADC, a low-power RTC, six general-purpose 16-bit timers including one PWM timer for motor control, two general-purpose 32-bit timers. They also feature standard and advanced communication interfaces.

- Up to three I²Cs
- Five SPIs
- Five I²Ss out of which two are full duplex. To achieve audio class accuracy, the I²S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Three USARTs
- SDIO interface
- USB 2.0 OTG full speed interface

Refer to [Table 2: STM32F411xC/xE features and peripheral counts](#) for the peripherals available for each part number.

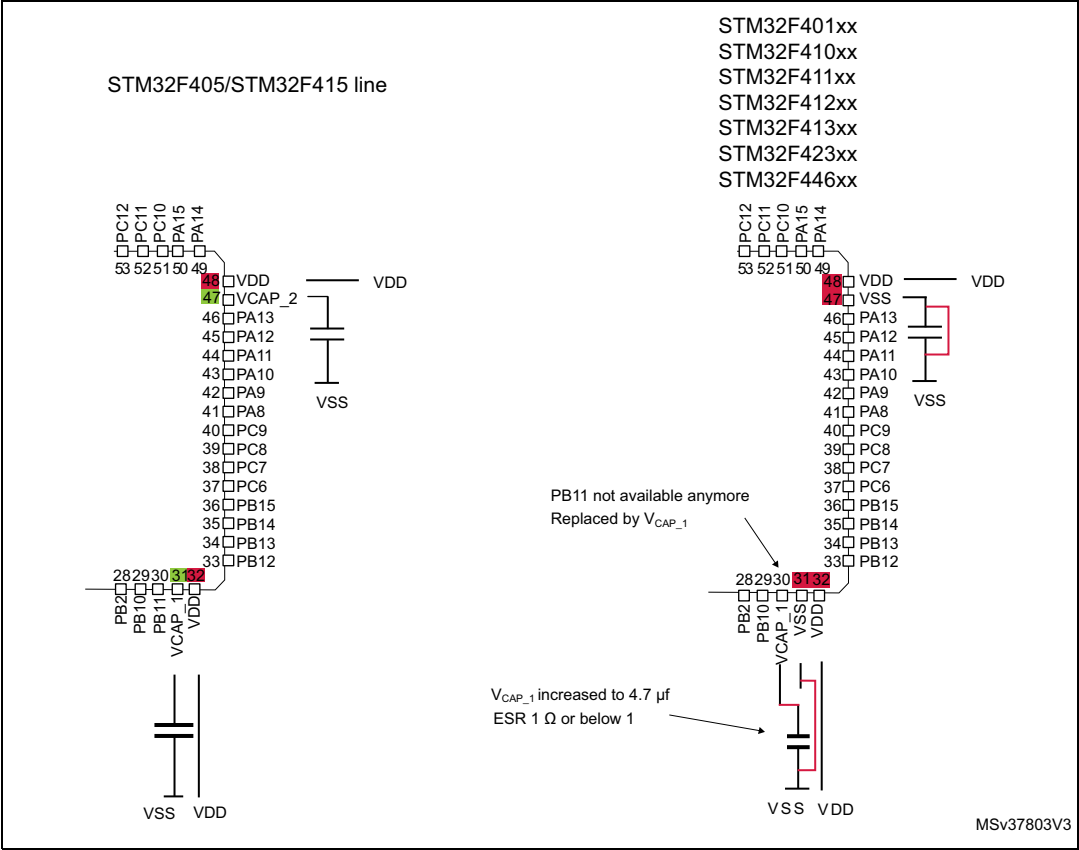
The STM32F411xC/xE operate in the - 40 to + 125 °C temperature range from a 1.7 (PDR OFF) to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.

These features make the STM32F411xC/xE microcontrollers suitable for a wide range of applications:

- Motor drive and application control
- Medical equipment
- Industrial applications: PLC, inverters, circuit breakers
- Printers, and scanners
- Alarm systems, video intercom, and HVAC
- Home audio appliances
- Mobile phone sensor hub

[Figure 3](#) shows the general block diagram of the devices.

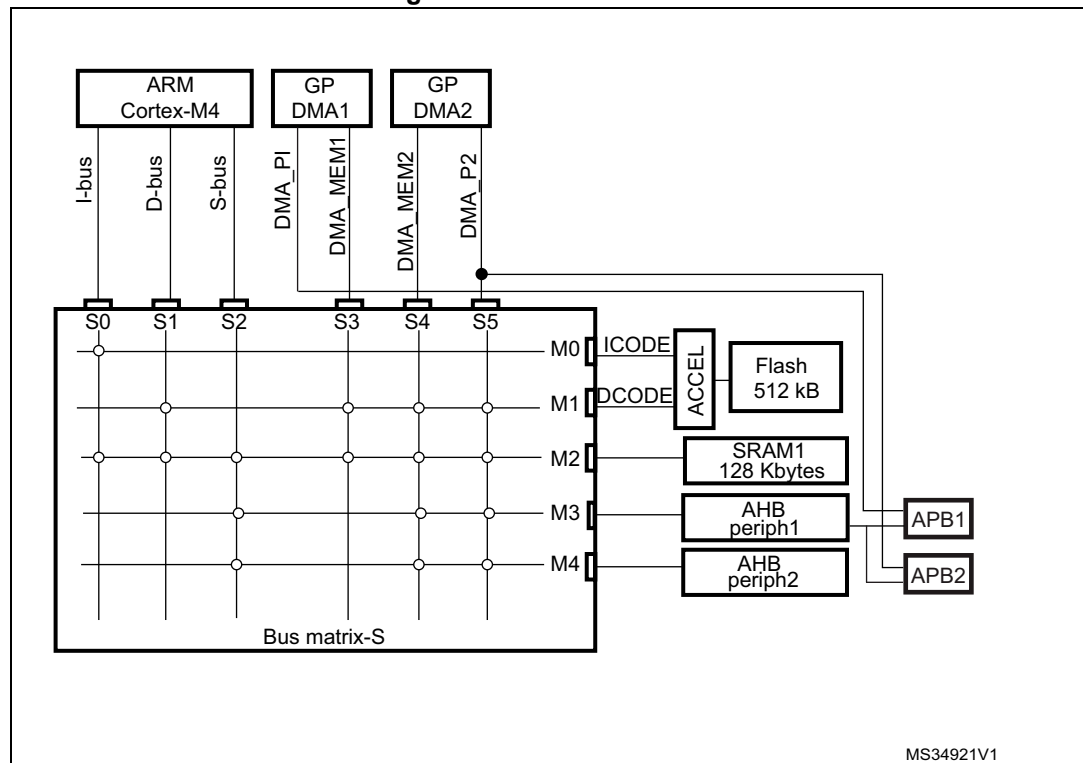
Figure 2. Compatible board design for LQFP64 package



3.8 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs) and the slaves (Flash memory, RAM, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

Figure 4. Multi-AHB matrix



3.9 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They feature dedicated FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.

Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. Configuration is made by software and transfer sizes between source and destination are independent.

buses is 100 MHz while the maximum frequency of the high-speed APB domains is 100 MHz. The maximum allowed frequency of the low-speed APB domain is 50 MHz.

The devices embed a dedicated PLL (PLL12S) which allows to achieve audio class performance. In this case, the I²S master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.

3.13 Boot modes

At startup, boot pins are used to select one out of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

The bootloader is located in system memory. It is used to reprogram the Flash memory by using USART1(PA9/10), USART2(PD5/6), USB OTG FS in device mode (PA11/12) through DFU (device firmware upgrade), I2C1(PB6/7), I2C2(PB10/3), I2C3(PA8/PB4), SPI1(PA4/5/6/7), SPI2(PB12/13/14/15) or SPI3(PA15, PC10/11/12).

For more detailed information on the bootloader, refer to Application Note: AN2606, *STM32™ microcontroller system memory boot mode*.

3.14 Power supply schemes

- VDD = 1.7 to 3.6 V: external power supply for I/Os with the internal supervisor (POR/PDR) disabled, provided externally through VDD pins. Requires the use of an external power supply supervisor connected to the VDD and NRST pins.
- V_{SSA}, V_{DDA} = 1.7 to 3.6 V: external analog power supplies for ADC, Reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively, with decoupling technique.
- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Refer to [Figure 17: Power supply scheme](#) for more details.

In addition to the audio PLL, a master clock input pin can be used to synchronize the I2S flow with an external PLL (or Codec output).

3.26 Secure digital input/output interface (SDIO)

An SD/SDIO/MMC/eMMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

The interface allows data transfer at up to 50 MHz, and is compliant with the SD Memory Card Specification Version 2.0.

The SDIO Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDIO/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

In addition to SD/SDIO/MMC/eMMC, this interface is fully compliant with the CE-ATA digital protocol Rev1.1.

3.27 Universal serial bus on-the-go full-speed (OTG_FS)

The devices embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 1.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG full-speed controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator. The major features are:

- Combined Rx and Tx FIFO size of 320 × 35 bits with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 4 bidirectional endpoints
- 8 host channels with periodic OUT support
- HNP/SNP/IP inside (no need for any external resistor)
- For OTG/Host modes, a power switch is needed in case bus-powered devices are connected

3.28 General-purpose input/outputs (GPIOs)

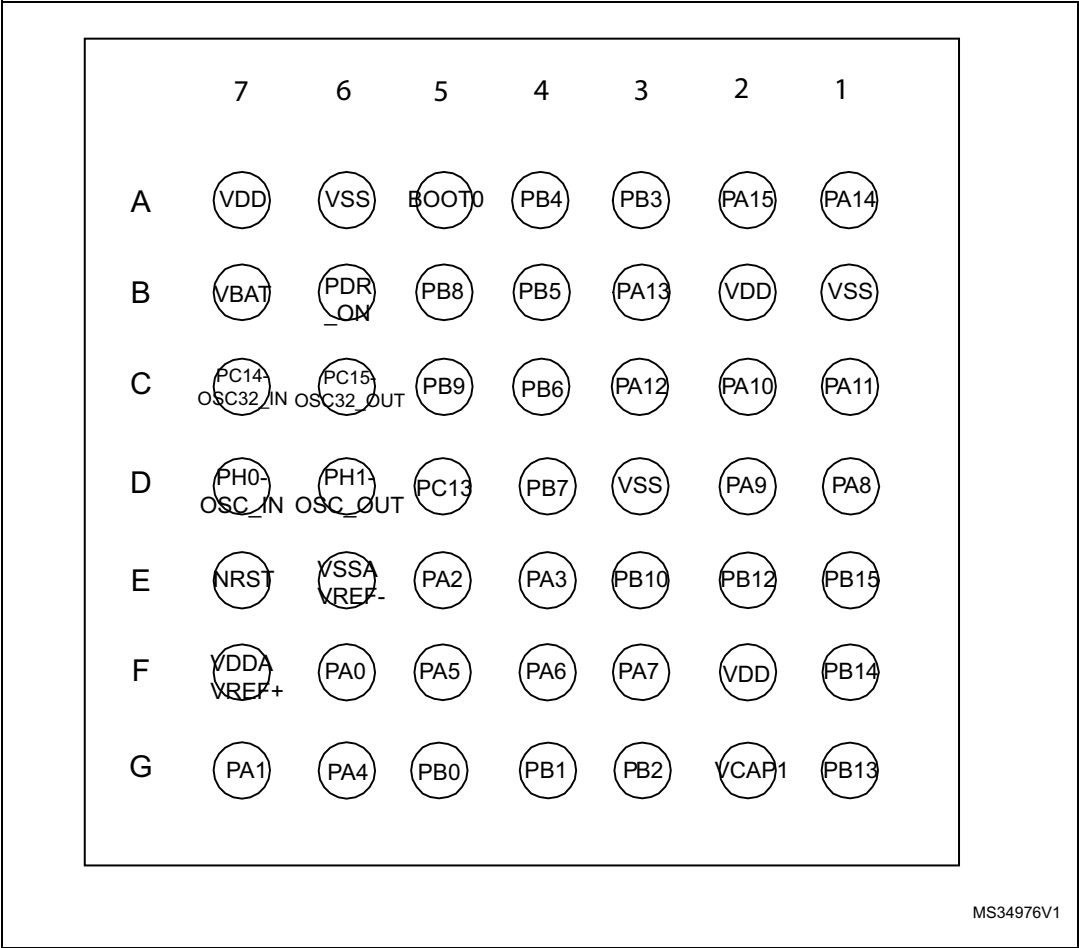
Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

Fast I/O handling allowing maximum I/O toggling up to 100 MHz.

4 Pinouts and pin description

Figure 9. STM32F411xC/xE WLCSP49 pinout



1. The above figure shows the package bump side.

Table 8. STM32F411xC/xE pin definitions (continued)

Pin number					Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP49	LQFP100	UFBGA100						
-	24	-	33	K5	PC4	I/O	FT	-	EVENTOUT	ADC1_14
-	25	-	34	L5	PC5	I/O	FT	-	EVENTOUT	ADC1_15
18	26	G5	35	M5	PB0	I/O	FT	-	TIM1_CH2N, TIM3_CH3, SPI5_SCK/I2S5_CK, EVENTOUT	ADC1_8
19	27	G4	36	M6	PB1	I/O	FT	-	TIM1_CH3N, TIM3_CH4, SPI5_NSS/I2S5_WS, EVENTOUT	ADC1_9
20	28	G3	37	L6	PB2	I/O	FT	-	EVENTOUT	BOOT1
-	-	-	38	M7	PE7	I/O	FT	-	TIM1_ETR, EVENTOUT	-
-	-	-	39	L7	PE8	I/O	FT	-	TIM1_CH1N, EVENTOUT	-
-	-	-	40	M8	PE9	I/O	FT	-	TIM1_CH1, EVENTOUT	-
-	-	-	41	L8	PE10	I/O	FT	-	TIM1_CH2N, EVENTOUT	-
-	-	-	42	M9	PE11	I/O	FT	-	TIM1_CH2, SPI4_NSS/I2S4_WS, SPI5_NSS/I2S5_WS, EVENTOUT	-
-	-	-	43	L9	PE12	I/O	FT	-	TIM1_CH3N, SPI4_SCK/I2S4_CK, SPI5_SCK/I2S5_CK, EVENTOUT	-
-	-	-	44	M10	PE13	I/O	FT	-	TIM1_CH3, SPI4_MISO, SPI5_MISO, EVENTOUT	-
-	-	-	45	M11	PE14	I/O	FT	-	TIM1_CH4, SPI4_MOSI/I2S4_SD, SPI5_MOSI/I2S5_SD, EVENTOUT	-
-	-	-	46	M12	PE15	I/O	FT	-	TIM1_BKIN, EVENTOUT	-



Table 9. Alternate function mapping (continued)

Port	AF00	AF01	AF02	AF03	AF04	AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15
	SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/I2S1S PI2/ I2S2/SPI3/ I2S3	SPI2/I2S2/ SPI3/ I2S3/SPI4/ I2S4/SPI5/ I2S5	SPI3/I2S3/ USART1/ USART2	USART6	I2C2/ I2C3	OTG1_FS		SDIO			
Port B	PB0	-	TIM1_CH2N	TIM3_CH3	-	-	-	SPI5_SCK /I2S5_CK	-	-	-	-	-	-	-	EVENT OUT
	PB1	-	TIM1_CH3N	TIM3_CH4	-	-	-	SPI5_NSS /I2S5_WS	-	-	-	-	-	-	-	EVENT OUT
	PB2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PB3	JTDO- SWO	TIM2_CH2	-	-	-	SPI1_SCK/ 2S1_CK	SPI3_SCK /I2S3_CK	USART1_ RX	-	I2C2_SDA	-	-	-	-	EVENT OUT
	PB4	JTRST		TIM3_CH1	-	-	SPI1_MISO	SPI3_MISO	I2S3ext_S D	-	I2C3_SDA			SDIO_ D0	-	EVENT OUT
	PB5	-	-	TIM3_CH2	-	I2C1_SMB A	SPI1_MOSI /I2S1_SD	SPI3_MOSI/ I2S3_SD		-	-	-	-	SDIO_ D3	-	EVENT OUT
	PB6	-	-	TIM4_CH1	-	I2C1_SCL	-	-	USART1_ TX	-	-	-	-		-	EVENT OUT
	PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_ RX	-	-	-	-	SDIO_ D0	-	EVENT OUT
	PB8	-	-	TIM4_CH3	TIM10_CH1	I2C1_SCL	-	SPI5_MOSI/ I2S5_SD	-	-	I2C3_SDA	-	-	SDIO_ D4	-	EVENT OUT
	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS/ 2S2_WS	-	-	-	I2C2_SDA	-	-	SDIO_ D5	-	EVENT OUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK/ 2S2_CK	I2S3_MCK	-	-	-	-	-	SDIO_ D7	-	EVENT OUT
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	I2S2_CKIN	-	-	-	-	-	-	-	-	EVENT OUT
	PB12	-	TIM1_BKIN	-	-	I2C2_SMB A	SPI2_NSS/ 2S2_WS	SPI4_NSS /I2S4_WS	SPI3_SCK /I2S3_CK	-	-	-	-	-	-	EVENT OUT
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK/ 2S2_CK	SPI4_SCK/ I2S4_CK	-	-	-	-	-	-	-	EVENT OUT
	PB14	-	TIM1_CH2N	-	-	-	SPI2_MISO	I2S2ext_SD	-	-	-	-	-	SDIO_ D6	-	EVENT OUT
	PB15	RTC_50H Z	TIM1_CH3N	-	-	-	SPI2_MOSI /I2S2_SD	-	-	-	-	-	-	SDIO_ CK	-	EVENT OUT

**Table 10. STM32F411xC/xE
register boundary addresses (continued)**

Bus	Boundary address	Peripheral
APB2	0x4001 5400 - 0x4001 FFFF	Reserved
	0x4001 5000 - 0x4001 53FFF	SPI5/I2S5
	0x4001 4800 - 0x4001 4BFF	TIM11
	0x4001 4400 - 0x4001 47FF	TIM10
	0x4001 4000 - 0x4001 43FF	TIM9
	0x4001 3C00 - 0x4001 3FFF	EXTI
	0x4001 3800 - 0x4001 3BFF	SYSCFG
	0x4001 3400 - 0x4001 37FF	SPI4/I2S4
	0x4001 3000 - 0x4001 33FF	SPI1/I2S1
	0x4001 2C00 - 0x4001 2FFF	SDIO
	0x4001 2400 - 0x4001 2BFF	Reserved
	0x4001 2000 - 0x4001 23FF	ADC1
	0x4001 1800 - 0x4001 1FFF	Reserved
	0x4001 1400 - 0x4001 17FF	USART6
	0x4001 1000 - 0x4001 13FF	USART1
	0x4001 0400 - 0x4001 0FFF	Reserved
	0x4001 0000 - 0x4001 03FF	TIM1
	0x4000 7400 - 0x4000 FFFF	Reserved

Table 16. VCAP_1/VCAP_2 operating conditions⁽¹⁾

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor with a single VCAP pin available	4.7 μ F
ESR	ESR of external capacitor with a single VCAP pin available	< 1 Ω

1. When bypassing the voltage regulator, the two 2.2 μ F V_{CAP} capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

6.3.3 Operating conditions at power-up/power-down (regulator ON)

Subject to general operating conditions for T_A .

Table 17. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	μ s/V
	V_{DD} fall time rate	20	∞	

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A .

Table 18. Operating conditions at power-up / power-down (regulator OFF)⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	μ s/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below 1.08 V.

Note: This feature is only available for UFBGA100 package.

Table 28. Typical and maximum current consumption in Stop mode - $V_{DD}=3.6\text{ V}$

Symbol	Conditions	Parameter	Typ	Max ⁽¹⁾					Unit
			T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	T _A = 125 °C		
I _{DD_STOP}	Flash in Stop mode, all oscillators OFF, no independent watchdog	Main regulator usage	113.7	145 ⁽²⁾	410	720 ⁽²⁾	1217	μA	
		Low power regulator usage	43.1	68 ⁽²⁾	310	600 ⁽²⁾	1073		
	Flash in Deep power down mode, all oscillators OFF, no independent watchdog	Main regulator usage	76.2	105 ⁽²⁾	320	600 ⁽²⁾	1019		
		Low power regulator usage	14	38 ⁽²⁾	275	560 ⁽²⁾	1025		
		Low power low voltage regulator usage	10	30 ⁽²⁾	235	510 ⁽²⁾	928		

1. Guaranteed by characterization results.

2. Guaranteed by test in production.

Table 29. Typical and maximum current consumption in Standby mode - $V_{DD}=1.7\text{ V}$

Symbol	Parameter	Conditions	Typ ⁽¹⁾	Max ⁽²⁾				Unit
			T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	T _A = 125 °C	
I _{DD_STBY}	Supply current in Standby mode	Low-speed oscillator (LSE) and RTC ON	2.4	4	12	25	50	μA
		RTC and LSE OFF	1.8	3 ⁽³⁾	11	24 ⁽³⁾	49	

1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2 μA .

2. Guaranteed by characterization results.

3. Guaranteed by test in production.

Table 30. Typical and maximum current consumption in Standby mode - $V_{DD}=3.6\text{ V}$

Symbol	Parameter	Conditions	Typ ⁽¹⁾	Max ⁽²⁾				Unit
			T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	T _A = 125 °C	
I _{DD_STBY}	Supply current in Standby mode	Low-speed oscillator (LSE) and RTC ON	2.8	5	14	29	59	μA
		RTC and LSE OFF	2.1	4 ⁽³⁾	13.5	28 ⁽³⁾	58	

1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2 μA .

2. Guaranteed by characterization results.

3. Guaranteed by test in production.

6.3.11 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see [Table 49: EMI characteristics for LQFP100](#)). It is available only on the main PLL.

Table 43. SSCG parameter constraints

Symbol	Parameter	Min	Typ	Max ⁽¹⁾	Unit
f_{Mod}	Modulation frequency	-	-	10	kHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP	(Modulation period) * (Increment Step)	-	-	$2^{15}-1$	-

1. Guaranteed by design.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$MODEPER = \text{round}[f_{PLL_IN} / (4 \times f_{Mod})]$$

f_{PLL_IN} and f_{Mod} must be expressed in Hz.

As an example:

If $f_{PLL_IN} = 1$ MHz, and $f_{MOD} = 1$ kHz, the modulation depth (MODEPER) is given by equation 1:

$$MODEPER = \text{round}[10^6 / (4 \times 10^3)] = 250$$

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$INCSTEP = \text{round}[(2^{15} - 1) \times md \times PLLN] / (100 \times 5 \times MODEPER)$$

f_{VCO_OUT} must be expressed in MHz.

With a modulation depth (md) = ± 2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$INCSTEP = \text{round}[(2^{15} - 1) \times 2 \times 240] / (100 \times 5 \times 250) = 126md(\text{quantitized})\%$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$md_{\text{quantized}}\% = (MODEPER \times INCSTEP \times 100 \times 5) / ((2^{15} - 1) \times PLLN)$$

As a result:

$$md_{\text{quantized}}\% = (250 \times 126 \times 100 \times 5) / ((2^{15} - 1) \times 240) = 2.002\%(\text{peak})$$

6.3.17 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 53](#)).

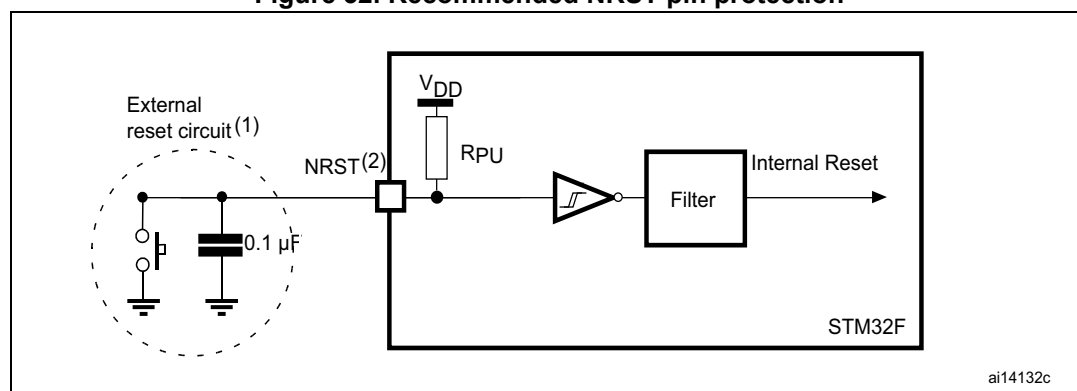
Unless otherwise specified, the parameters given in [Table 56](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#). Refer to [Table 53: I/O static characteristics](#) for the values of V_{IH} and V_{IL} for NRST pin.

Table 56. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor ⁽¹⁾	$V_{IN} = V_{SS}$	30	40	50	$k\Omega$
$V_{F(NRST)}^{(2)}$	NRST Input filtered pulse		-	-	100	ns
$V_{NF(NRST)}^{(2)}$	NRST Input not filtered pulse	$V_{DD} > 2.7\text{ V}$	300	-	-	ns
T_{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	-	μs

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).
2. Guaranteed by design.

Figure 32. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 56](#). Otherwise the reset is not taken into account by the device.

6.3.22 V_{BAT} monitoring characteristics

Table 73. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	50	-	K Ω
Q	Ratio on V_{BAT} measurement	-	4	-	
$E_r^{(1)}$	Error on Q	-1	-	+1	%
$T_{S_vbat}^{(2)(2)}$	ADC sampling time when reading the V_{BAT} 1 mV accuracy	5	-	-	μ s

1. Guaranteed by design.
2. Shortest sampling time can be determined in the application by multiple iterations.

6.3.23 Embedded reference voltage

The parameters given in [Table 74](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

Table 74. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	- 40 °C < T_A < + 125 °C	1.18	1.21	1.24	V
$T_{S_vrefint}^{(1)}$	ADC sampling time when reading the internal reference voltage	-	10	-	-	μ s
$V_{RERINT_s}^{(2)}$	Internal reference voltage spread over the temperature range	$V_{DD} = 3V \pm 10mV$	-	3	5	mV
$T_{Coeff}^{(2)}$	Temperature coefficient	-	-	30	50	ppm/°C
$t_{START}^{(2)}$	Startup time	-	-	6	10	μ s

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design.

Table 75. Internal reference voltage calibration values

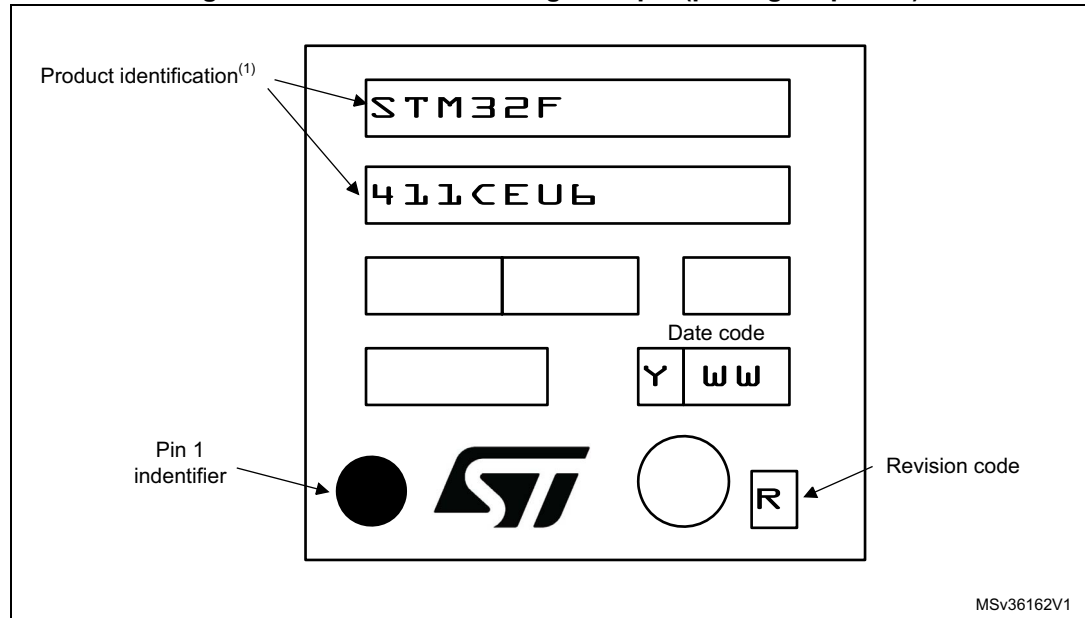
Symbol	Parameter	Memory address
V_{REFIN_CAL}	Raw data acquired at temperature of 30 °C $V_{DDA} = 3.3$ V	0x1FFF 7A2A - 0x1FFF 7A2B

Device marking for UFQFPN48

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

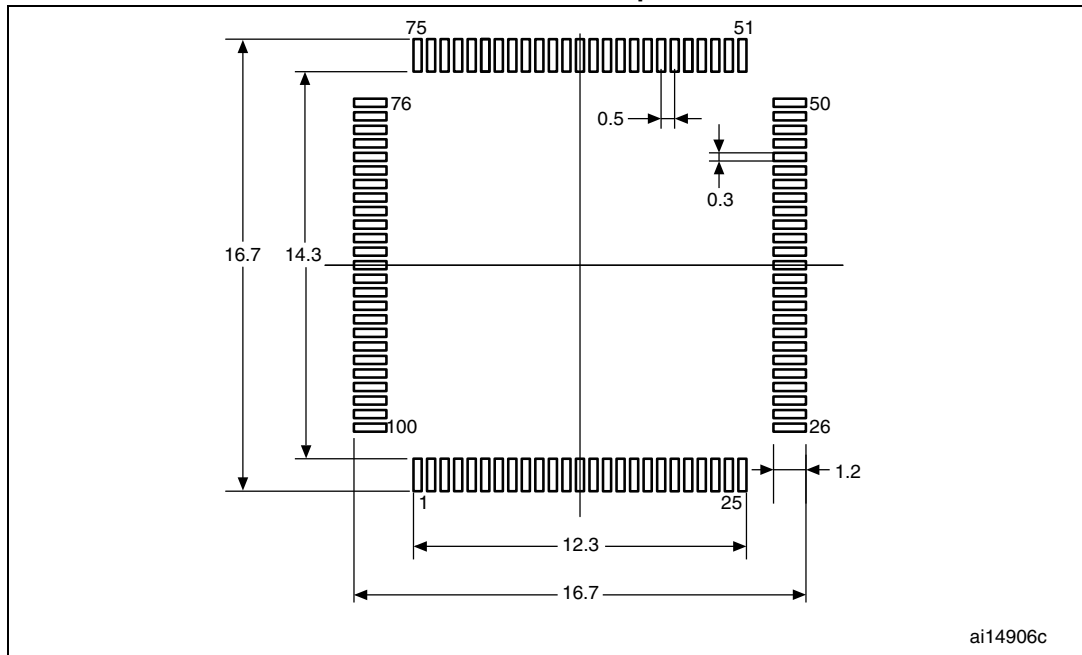
Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 51. UFQFPN48 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Figure 56. LQFP100 - 100-pin, 14 x 14 mm, 100-pin low-profile quad flat recommended footprint



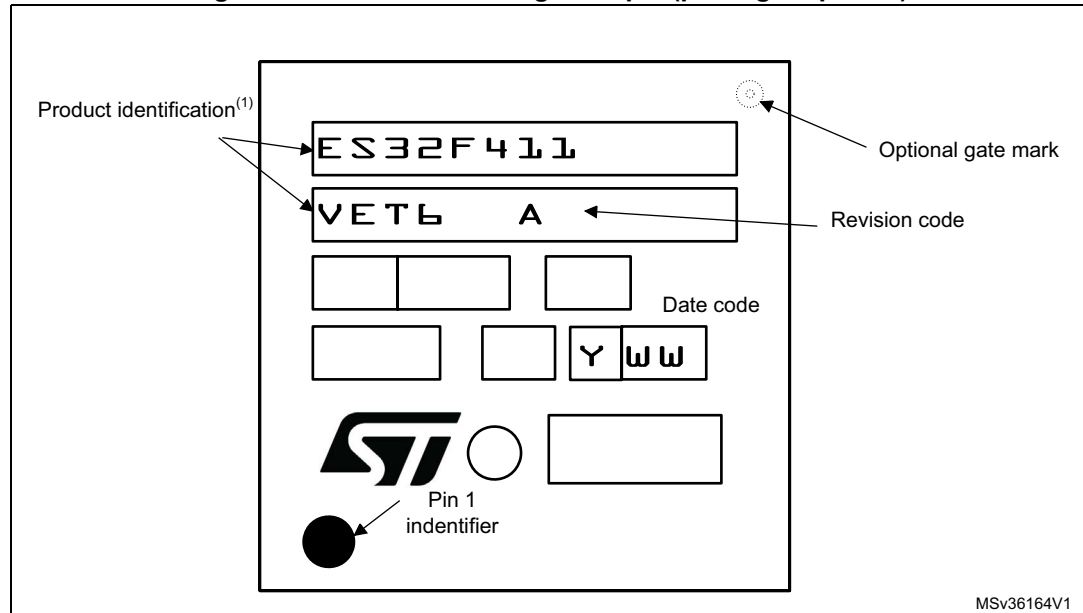
1. Dimensions are in millimeters.

Device marking for LQFP100

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 57. LQPF100 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.5 UFBGA100 package information

Figure 58. UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline

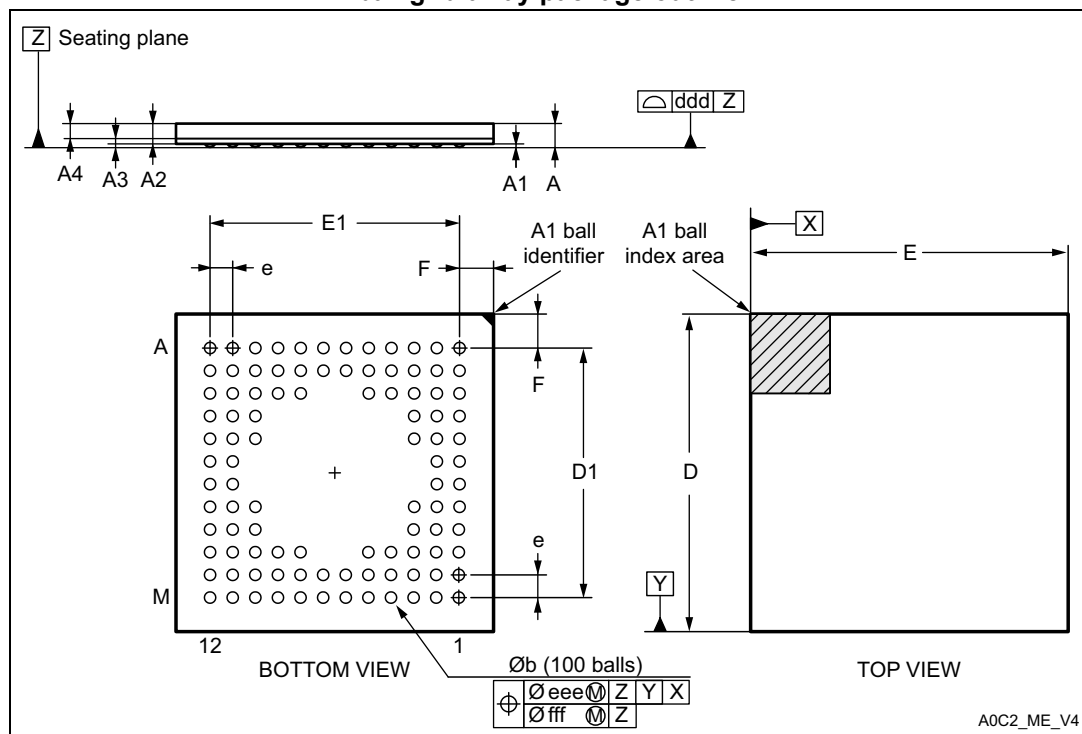


Table 84. UFBGA100, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A3	-	0.130	-	-	0.0051	-
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
D	6.950	7.000	7.050	0.2736	0.2756	0.2776
D1	5.450	5.500	5.550	0.2146	0.2165	0.2185
E	6.950	7.000	7.050	0.2736	0.2756	0.2776
E1	5.450	5.500	5.550	0.2146	0.2165	0.2185
e	-	0.500	-	-	0.0197	-
F	0.700	0.750	0.800	0.0276	0.0295	0.0315

Table 88. Document revision history

Date	Revision	Changes
21-Nov-2016	5	<p>Updated:</p> <ul style="list-style-type: none"> – Features – Figure 1: Compatible board design for LQFP100 package – Figure 2: Compatible board design for LQFP64 package – Figure 3: STM32F411xC/xE block diagram – Figure 22: High-speed external clock source AC timing diagram – Figure 23: Low-speed external clock source AC timing diagram – Figure 33: I2C bus AC waveforms and measurement circuit – Figure 58: UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline – Table 2: STM32F411xC/xE features and peripheral counts – Table 8: STM32F411xC/xE pin definitions – Table 13: Thermal characteristics – Table 14: General operating conditions – From Table 20: Typical and maximum current consumption, code with data processing (ART accelerator disabled) running from SRAM - VDD = 1.7 V to Table 31: Typical and maximum current consumptions in VBAT mode – Table 35: High-speed external user clock characteristics – Table 36: Low-speed external user clock characteristics – Table 39: HSI oscillator characteristics – Table 47: Flash memory endurance and data retention – Table 51: Electrical sensitivities – Table 53: I/O static characteristics – Table 76: Dynamic characteristics: SD / MMC characteristics – Table 86: Ordering information scheme <p>Added:</p> <ul style="list-style-type: none"> – One-time programmable bytes – Table 85: Package thermal characteristics
05-Dec-2016	6	<p>Updated:</p> <ul style="list-style-type: none"> – Table 27: Typical and maximum current consumptions in Stop mode - VDD = 1.7 V – Table 28: Typical and maximum current consumption in Stop mode - VDD=3.6 V – Table 29: Typical and maximum current consumption in Standby mode - VDD= 1.7 V – Table 30: Typical and maximum current consumption in Standby mode - VDD= 3.6 V